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a first pixel electrode over the second insulating film,
wherein the first pixel electrode is electrically con-
nected to the active layer; and
a second pixel electrode adjacent to the first pixel elec-
trode over the second insulating film, 5
wherein the first channel forming region overlaps with the
wiring, the second channel forming region does not
overlap with the wiring, and the second pixel electrode
overlaps with a portion of the active la er between the
first channel forming region and the second channel 10
forming region.

8. The electronic device according to claim 7, wherein the
first insulating film comprises silicon oxide.

9. The electronic device according to claim 7, wherein the
first insulating film comprises a first insulating layer com- 15
prising silicon nitride and a second insulating layer com-
prising silicon oxide on the first insulating layer.

10. The electronic device according to claim 7, wherein
the first pixel electrode comprises Ag.

11. The electronic device according to claim 7, further 20
comprising a capacitor having the first insulating film as a
dielectric layer between a portion of the active layer and a
capacitor wiring.

12. The electronic device according to claim 7, wherein 25
the first pixel electrode and the wiring are in contact with an
upper surface of the second insulating film.

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